

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage $V_{CE0} = 140\text{ V}$
- Typical $f_t = 20\text{ MHz}$
- Fully characterized at $125\text{ }^\circ\text{C}$

Application

- Power supply

Description

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

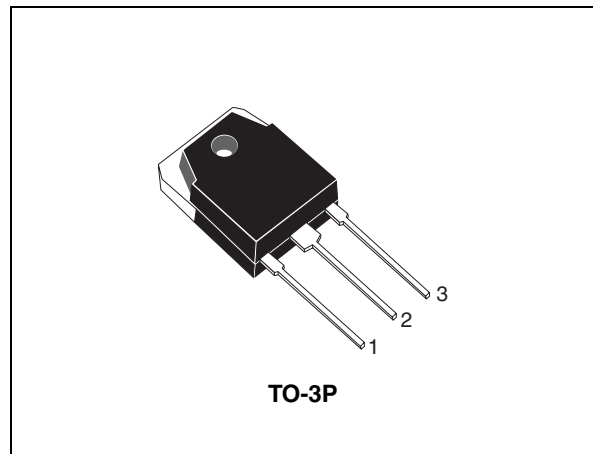


Figure 1. Internal schematic diagram

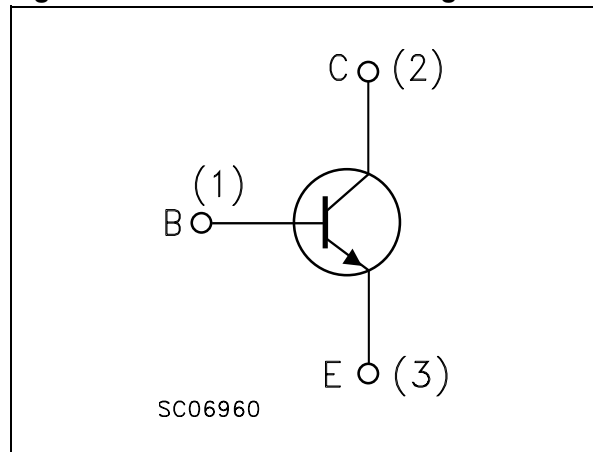


Table 1. Device summary

Order code	Marking	Package	Packaging
2SD1047	2SD1047	TO-3P	Tube

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	200	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	140	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	6	V
I_C	Collector current	12	A
I_{CM}	Collector peak current ($t_p < 5$ ms)	20	A
P_{tot}	Total dissipation at $T_c = 25$ °C	100	W
T_{stg}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.25	°C/W

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 200\text{ V}$			0.1	μA
I_{EBO}	Emitter cut-off current ($I_{\text{C}} = 0$)	$V_{\text{EB}} = 6\text{ V}$			0.1	μA
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 50\text{ mA}$	140			V
$V_{(\text{BR})\text{CBO}}$	Collector-base breakdown voltage ($I_{\text{E}} = 0$)	$I_{\text{C}} = 100\ \mu\text{A}$	200			V
$V_{(\text{BR})\text{EBO}}^{(1)}$	Emitter-base breakdown voltage ($I_{\text{C}} = 0$)	$I_{\text{E}} = 1\text{ mA}$	6			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 5\text{ A}$ $I_{\text{B}} = 500\text{ mA}$ $I_{\text{C}} = 7\text{ A}$ $I_{\text{B}} = 700\text{ mA}$			0.5 0.7	V V
V_{BE}	Base-emitter voltage	$V_{\text{CE}} = 5\text{ V}$ $I_{\text{C}} = 5\text{ A}$			1.3	V
h_{FE}	DC current gain	$I_{\text{C}} = 1\text{ A}$ $V_{\text{CE}} = 5\text{ V}$ $I_{\text{C}} = 5\text{ A}$ $V_{\text{CE}} = 4\text{ V}$	60 50		200	
f_{T}	Transition frequency	$I_{\text{C}} = 0.5\text{ A}$ $V_{\text{CE}} = 12\text{ V}$		20		MHz
C_{CBO}	Collector-base capacitance ($I_{\text{E}} = 0$)	$V_{\text{CB}} = 10\text{ V}$ $f = 1\text{ MHz}$		150		pF
t_{on} t_{stg} t_{f}	Resistive Load Turn-on time Storage time Fall time	$V_{\text{CC}} = 60\text{ V}$ $I_{\text{C}} = 5\text{ A}$ $I_{\text{B1}} = -I_{\text{B2}} = 0.5\text{ A}$		0.22 4.3 0.5		μs μs μs

1. Pulse duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

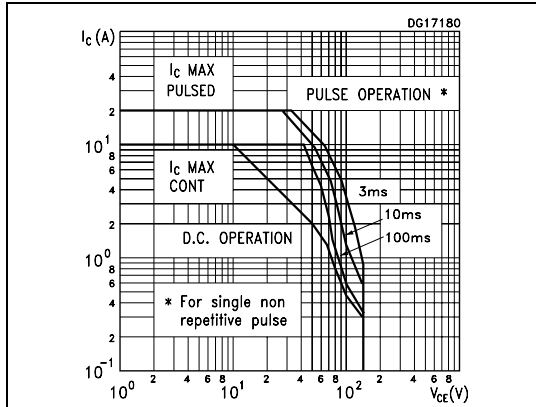


Figure 3. Output characteristics

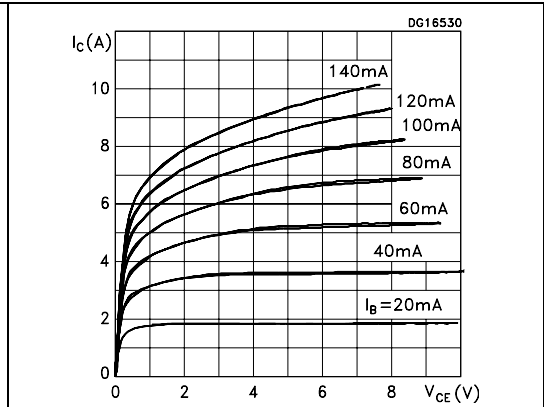


Figure 4. DC current gain

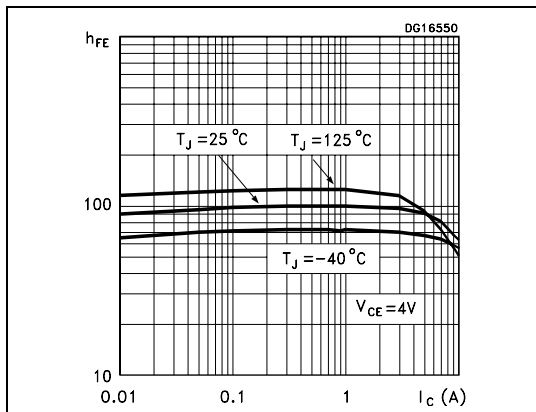


Figure 5. Collector-emitter saturation voltage

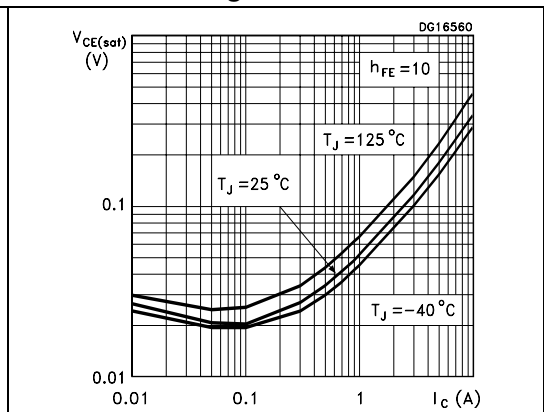


Figure 6. Base-emitter voltage

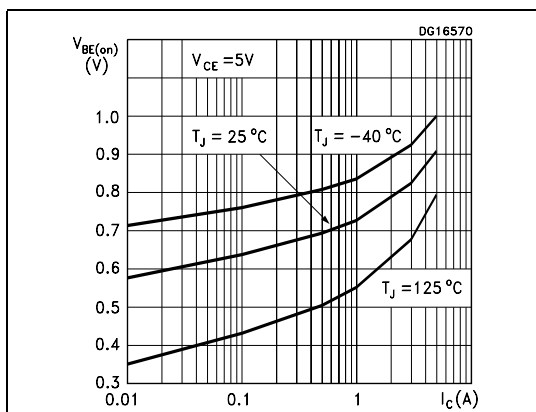
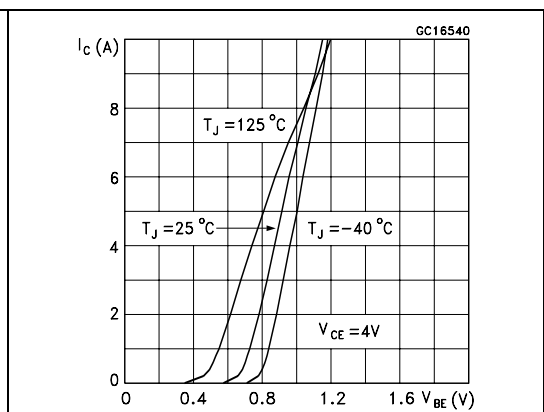


Figure 7. Base-emitter voltage



2.2 Test circuit

Figure 8. Resistive load switching test circuit

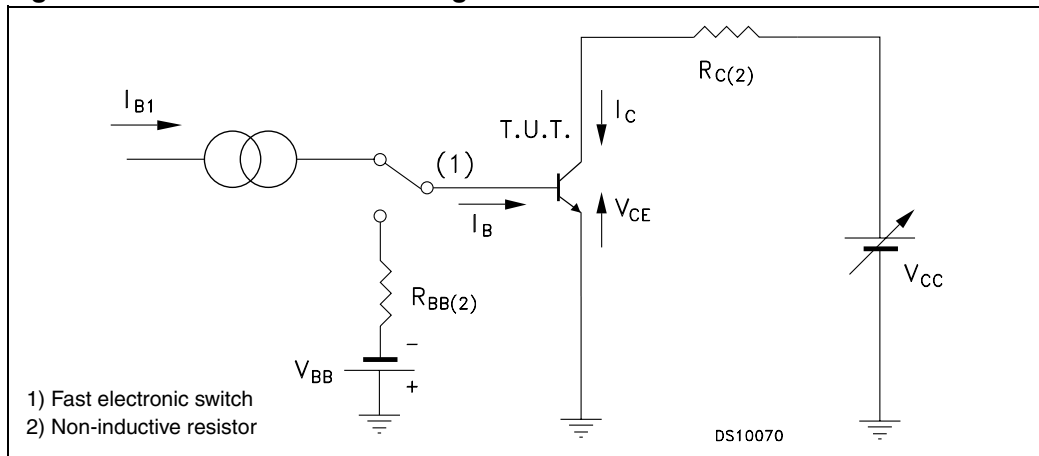


Table 5. TO-3P mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.6		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
P	3.10		3.30
Q		5	
Q1		3.80	

Figure 9. TO-3P drawings

